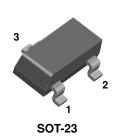
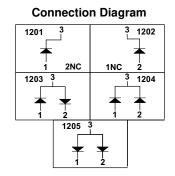


MMBD1201 / MMBD1202 / MMBD1203 / MMBD1204 / MMBD1205 Small Signal Diodes





Ordering Information

| Part Number | Top Mark | Package | Packing Method |
|-------------|----------|-----------|----------------|
| MMBD1201 | 24 | SOT-23 3L | Tape and Reel |
| MMBD1202 | 25 | SOT-23 3L | Tape and Reel |
| MMBD1203 | 26 | SOT-23 3L | Tape and Reel |
| MMBD1204 | 27 | SOT-23 3L | Tape and Reel |
| MMBD1205 | 28 | SOT-23 3L | Tape and Reel |

Absolute Maximum Ratings(1), (2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25$ °C unless otherwise noted.

| Symbol | Parameter | | Value | Unit |
|--------------------|--|-------------------------------|-------------|------|
| V _{RRM} | Maximum Repetitive Reverse Voltage | | 100 | V |
| I _{F(AV)} | Average Rectified Forward Current | | 200 | mA |
| I _{FSM} | Non-Repetitive Peak Forward Surge Current | Pulse Width = 1.0 second | 1.0 | A |
| | | Pulse Width = 1.0 microsecond | 2.0 | |
| T _{STG} | Storage Temperature Range | | -55 to +150 | °C |
| TJ | Operating Junction Temperature | | 150 | °C |

Notes

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or lowduty-cycle operations.

Thermal Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

| Symbol | Parameter | Value | Unit |
|-----------------|---|-------|-------|
| P _D | Power Dissipation | 350 | mW |
| | Derate Above 25°C | 2.8 | mW/°C |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | 357 | °C/W |

Electrical Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Conditions | Min. | Max. | Unit |
|-----------------|-----------------------|---|------|------|------|
| V _R | Breakdown Voltage | I _R = 100 μA | 100 | | V |
| | Forward Voltage | I _F = 1.0 mA | 550 | 600 | mV |
| V_F | | I _F = 10 mA | 660 | 740 | mV |
| | | I _F = 100 mA | 820 | 920 | mV |
| | | I _F = 200 mA | 0.87 | 1.0 | V |
| | | I _F = 300 mA | | 1.1 | V |
| | Reverse Current | V _R = 20 V | | 25 | nA |
| I _R | | V _R = 50 V | | 50 | nA |
| | | V _R = 50 V, T _A = 150°C | | 100 | μΑ |
| C _T | Total Capacitance | V _R = 0, f = 1.0 MHz | | 2.0 | pF |
| t _{rr} | Reverse Recovery Time | $I_F = I_R = 10 \text{ mA}, I_{RR} = 1.0 \text{ mA},$ $R_L = 100 \Omega$ | | 4.0 | nS |

Typical Performance Characteristics

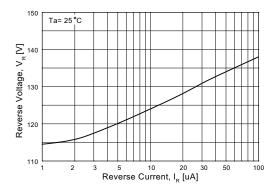


Figure 1. Reverse Voltage vs. Reverse Current BV @ $I_R = 1.0$ to 100 A

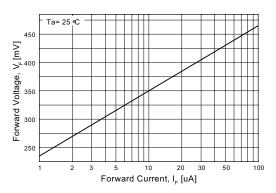


Figure 3. Forward Voltage vs. Forward Current $V_F @ I_F = 1.0 \text{ to } 100 \text{ A}$

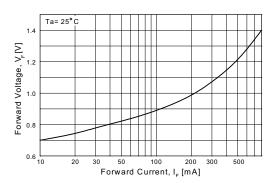


Figure 5. Forward Voltage vs. Forward Current $V_F @ I_F = 10 \text{ to } 800 \text{ mA}$

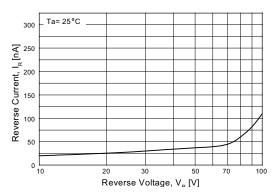


Figure 2. Reverse Current vs. Reverse Voltage $I_R @ \ V_R = 10 \ to \ 100 \ V$

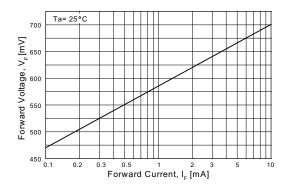


Figure 4. Forward Voltage vs. Forward Current $V_F @ I_F = 0.1$ to 10 mA

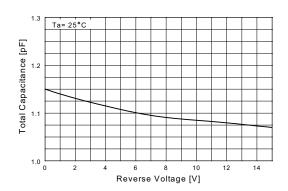


Figure 6. Total Capacitance vs. Reverse Voltage

Typical Performance Characteristics (Continued)

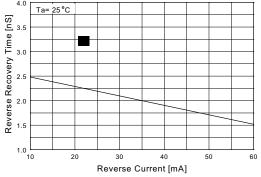


Figure 7. Reverse Recovery Time vs. Reverse Current

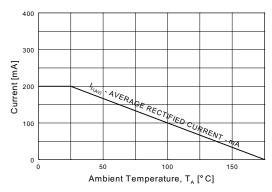


Figure 8. Average Rectified Current ($I_{F(AV)}$) vs. Ambient Temperature (T_A)

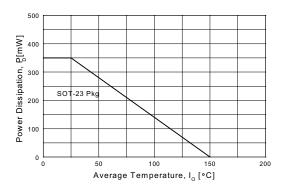


Figure 9. Power Derating Curve

Physical Dimensions 0.95 2.92±0.20 3 1.40 1.30^{+0.20}_{-0.15} 2.20 0.60 0.37 (0.29) -0.95 ⊕ | 0.20 M | A | B -1.00 1.90 1.90 LAND PATTERN RECOMMENDATION SEE DETAIL A 1.20 MAX 0.10 (0.93) □ 0.10 M C С 2.40±0.30 NOTES: UNLESS OTHERWISE SPECIFIED **GAGE PLANE** A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H. B) ALL DIMENSIONS ARE IN MILLIMETERS. 0.23 0.08 C) DIMENSIONS ARE INCLUSIVE OF BURRS, 0.25 MOLD FLASH AND TIE BAR EXTRUSIONS. D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994. 0.20 MIN **SEATING** E) DRAWING FILE NAME: MA03DREV10 **PLANE** (0.55)**DETAIL A** SCALE: 2X

Figure 10. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

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